Embedded anisotropic microreflectors by femtosecond-laser nanomachining

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Directly written embedded structures created within fused silica by a femtosecond Ti:sapphire laser are observed to strongly reflect blue light. Reflection emerges only in a direction parallel to the polarization axis of the writing laser. This anisotropic-effect is caused by a periodic modulation of refractive index of amplitude $\Delta n \sim 10^{-2}$ with a characteristic period $\Lambda \sim 150$ nm over a spot size $\sim 1.5 \ \mu$ m. We show that the origin of the anisotropic reflection is the primary cause of other anisotropic phenomena reported in recent experiments. © 2002 American Institute of Physics. [DOI: 10.1063/1.1492004]

The use of a femtosecond laser source to directly write structures deep within transparent media has recently attracted much attention due to its simplicity compared to lithographic methods, and its capability for writing in three dimensions.¹⁻³ Tight focusing of the laser into the bulk of material causes nonlinear absorption only within the focal volume, depositing energy that induces a permanent material modification.^{4,5} A variety of photonic devices have already been created by translating a sample through the focus of a femtosecond laser.^{6,7} Although molecular defects caused by such intense irradiation have been identified in fluorescence, electron-spin resonance and other studies,⁸ the mechanism of induced modifications in glass is still not fully understood. Moreover, such structures in Ge-doped silica⁹ and other glass materials¹⁰ show an unexpected anisotropic light scattering which is dependent on the plane of light polarization. This has been interpreted in terms of photoelectrons moving along the direction of light polarization inducing index inhomogenities. More recently, uniaxial birefringence imprinted in structures written within fused silica plates has been observed but the origin of this anisotropic phenomenon remains a mystery.¹¹ In this letter, we will describe a further anisotropic property observed in silica after being irradiated by a femtosecond laser-strong reflection from the modified region occurring only along the direction of polarization of the writing laser. Our analysis suggests that this effect is also the primary cause of all previously reported anisotropic phenomena.

A regeneratively amplified mode-locked Ti:sapphire laser (150 fs pulse duration, 250 kHz repetition rate) operating at $\lambda = 850$ nm was used to directly write microstructures into a fused silica plate $(40 \times 40 \times 1 \text{ mm})$. In the experimental arrangement (Fig. 1), the collimated laser passes through an electronic shutter, variable neutral density filter and halfwave plate before a dichroic mirror reflecting only in the 400-700 nm region. The infrared laser light travels through and is focused through а the mirror 50 \times (numerical aperture=0.55) objective into the bulk of the sample, down to a beam waist diameter estimated to be $\sim 1.5 \ \mu$ m. The silica sample is mounted on a computer-controlled linear-motor three-dimensional translation stage (of 20 nm resolution). To simultaneously observe the writing process, a charge coupled device camera with suitable filters and white light source is used.

A range of embedded diffraction gratings with overall dimensions 700 μ m \times 700 μ m, each consisting of 100 rulings with 7 μ m period were directly written towards the edges of the plate at a depth of 0.5 mm below the front surface. In every case, the speed of writing was 200 μ m/s and each grating ruling had only one pass of the laser. Pairs of embedded gratings were created with orthogonal writing polarizations directed parallel and perpendicular to the grating rulings, respectively, with average fluence ranging from 270 mW (~1.1 μ J/pulse) down to 26 mW (~0.1 μ J/pulse). Additionally, pairs of embedded single lines of length 1 mm were written by the same method. Finally, a regular array of 40×40 "dots" with a pitch of 10 μ m was directly written into the corner of the plate. Each dot was produced by holding the sample translation stage stationary at each writing point, and irradiating for 3 ms (\sim 750 pulses) using the electronic shutter.

After writing, the samples were viewed through the silica plate's polished edges using a $200 \times$ microscope incor-



FIG. 1. Experimental setup for short-pulse direct writing of embedded structures.

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FIG. 2. Schematic showing the anisotropic reflection from embedded photonic structures. Reflection only occurs for incident light parallel to the electric-field vector of the incident writing laser. The magnified region (bottom) illustrates the laser-induced self-organized periodic nanostructuring responsible. wl: unpolarized white light, br: blue reflection, k_w : incident direct-write laser.

porating a color charge coupled device camera. During inspection, the structures were illuminated with a randomly polarized white light source in a direction along the viewing axis, either from below the structure (opposite side to microscope objective), or above the structure (through the microscope objective). The embedded structures were examined through the edge nearest to them, and the array of dots was examined in two orthogonal directions. A striking reflection was observed in the blue spectral region from a number of the structures when illuminated via the viewing objective. Closer analysis revealed that the reflection only occurred when the viewing axis was both parallel to the electric field vector of the writing beam and the structure was written with pulse energy greater than $\sim 0.5 \ \mu$ J. This indicates that the observed reflectivity is both fluence dependent and highly anisotropic. Fluorescence cannot account for the observation due to the directional dependence. Figure 2 shows a schematic of the reflection phenomenon. As can be seen, the macroscopic shape of the photonic structures does not determine the direction of the anisotropic reflection.

Figure 3 shows microscope images of the reflection from several directly written embedded structures. The illuminating light in all cases was incident above the samples through the viewing objective and set to a level that ensured that the weak-contrast microstructure itself was not imaged. The spatial position of the embedded objects relative to the focus of the microscope objective was checked beforehand by illuminating from below, when the embedded structure in all cases could be clearly observed. The displayed images were chosen from regions of modification created with a pulse energy of ~0.9 μ J. In each example the orientation of the direct-write laser's electric field is indicated, while the \mathbf{k}_w vector



FIG. 3. Charged coupled device camera images of the reflection from different embedded structures directly written with the laser (incident direction k_w , polarization orientation *E*). (a) Reflection from a single line, (b) reflection from 100 lines one behind another into the page, (c) identical structure to (b) showing no reflection. (d), (e) Array of dots which show reflectivity dependent only on the writing polarization orientation.

marks the incident direction of the writing laser beam. Figure 3(a) displays the reflection from a single line which has dimensions $\sim 1.5 \ \mu m$ into the page due to the focal width of the beam, and $\sim 30 \ \mu m$ down the page due to the beam's confocal parameter, enhanced by self-focusing effects.⁵ Figure 3(b) shows the reflection from the side of a 100-line grating, with its rulings going into the depth of the page. Not all of the 100 lines of the grating contribute to the recorded reflection because of the ${\sim}2~\mu{\rm m}$ focal depth of the imaging objective. Nevertheless, the reflection is considerably enhanced compared to the single line in Fig. 3(a). Figure 3(c)shows the result of imaging an identical structure to Fig. 3(b), except written with orthogonal polarization. From this orientation, no reflecting structure at all can be observed. Figure 3(d) shows a section of the 40×40 array of dots described earlier, once again producing strong reflection along the writing beam polarization axis. These particular structures are interesting because they are approximately circular with a diameter of $\sim 1.5 \ \mu m$ when viewed from the direction of the writing laser, and therefore have a uniform cross section. However, when viewed from a direction orthogonal to the axis of the writing beam's polarization, there is no reflecting component as Fig. 3(e) clearly demonstrates. The reflected light observed from the structure shown in Fig. 3(b) is analyzed yielding the spectrum displayed in Fig. 4. This data show a strong peak at 460 nm, which accounts for the

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FIG. 4. Spectrum of the reflected light from the structure shown in Fig. 3(b).

blue color when observed under a microscope.

We suggest that the anisotropic reflectivity can only be explained as a consequence of Bragg reflection from a selforganized periodic structure. Indeed, a modulation in refractive index of period $\Lambda \sim 150$ nm, produced only along the direction of the incident laser's electric field can account for the observed anisotropic reflection at $\lambda \sim 460 \text{ nm}$ (A) $=\lambda/2n$). Such a grating does not reflect when viewed edge on. The magnified section at the bottom right-hand corner of Fig. 2 demonstrates how the periodic nanostructuring is arranged in the case of a single 1.5 μ m diameter dot. The orientation of the nanostructure is identical to that implicated in our previous publication describing the empirical observation of anisotropic light scattering. Evidence was given here of index inhomogeneities with a period estimated to be ~ 90 nm.9 Closer inspection of Fig. 4 shows an additional smaller peak at 835 nm. This suggests that an extra grating component may be formed which has double the periodicity of the laser-induced structures. Alternatively, this long-wavelength reflection could be a second-order diffraction peak of a grating component with period equal to the wavelength of the incident light.¹² Surface ripples with a period equal to the wavelength of incident laser radiation and that are likewise aligned in a direction orthogonal to the electric field have been observed in experiments involving laser deposition.¹² Nevertheless, we believe that our data is evidence of periodic nanostructures (much smaller than the wavelength of incident light) being generated within the bulk of a material. We speculate they arise from a mechanism associated with the creation of a hot electron plasma by multiphoton absorption of incident light. Anisotropic index inhomogeneities are then induced by electrons moving along the direction of light polarization.9 By analogy to the mechanism ascribed to cause surface ripples on materials (i.e., interference initiated by a coupling between incident laser and a surface-plasma wave),¹² we further suggest that the self-organized nanostructures are similarly produced by a pattern of interference between the incident laser radiation and a plasmon-polarition wave generated within the sample. Positive feedback leads to exponential growth of the periodic nanostructures in the plane of light polarization, which become frozen within the material.

Further microscope characterization was carried out on

the same samples by positioning the fused silica plate be-

tween crossed polarizers and illuminating from below along the direction of the original writing beam. With the polarizers oriented at angles of $\pm \pi/4$ to the writing-beam electric-field vector, this enables regions of birefringence to be identified. The onset of birefringence occurs at a writing-fluence level ~0.5 µJ/pulse, equal to that found in the case of the anisotropic reflection.¹¹ This strongly suggests that the mechanism responsible for inducing reflection along the writing beam polarization axis is the same mechanism that causes birefringence in the orthogonal direction. The femtosecond-laserinduced birefringence, which up to now has not been well understood, is therefore likely to be caused by the laterally oriented small-period grating structures. Birefringence of this nature is well known as "form" birefringence.¹³

Reflectivity measurements made from the side of a macroscopic grating as shown in Fig. 3(b) give a value of $\sim 1\%$ per 1.5 μ m long micrograting. Given that each micrograting contains ten periods of refractive-index modulation across its 1.5 μ m width, the maximum reflectivity

$$R_{\rm max} = {\rm tanh}^2 \left(\frac{\pi \, \delta n L}{\lambda_{\rm reflection}} \right),$$

where *L* is the length of the reflecting region and $\lambda_{\text{reflection}}$ is 460 nm, implies that the amplitude of index variation, $\delta n \sim 0.01$. This also suggests that it is possible to achieve much higher reflectivities by increasing the depth of the writing laser irradiated spot.

In conclusion, we have directly written submicron photonic structures into the internal bulk of fused silica with a femtosecond laser system. The nanostructures are observed to strongly reflect in the blue spectral region but only along the polarization axis of the original writing beam. We show this can arise from a self-organized periodic refractive index modulation. The effect can explain systematically the origin of other observed anisotropic behavior reported with such pulsed laser patterning. The anisotropic microreflectors described here should be useful in many monolithic photonic devices and can be harnessed for information storage, microelectromechanical systems applications or quasiphase matching where nanoscale periodic structuring is required.

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